WHAT IS CLAIMED IS:

1. A water production system comprising:

a filter unit that filters water to produce clear water;

an ultraviolet light irradiator that irradiates, with ultraviolet light, the clear water produced by the filter unit, thereby degrading organic matter in the clear water;

an ion exchange resin unit that purifies the clear water, in which the organic matter has been degraded by the ultraviolet light irradiator, into pure water; and

a deaerated water production unit that deaerates the pure water to produce deaerated water,

wherein the deaerated water production unit includes a chamber, a water receiving port through which the pure water is received into the chamber, a depressurizer that reduces pressure in the chamber, an ultrasonic oscillator that applies ultrasonic waves to the pure water in the chamber, and a deaerated water outflow port through which the deaerated water flows out of the chamber.

2. The water production system according to claim 1, further comprising a microfilter arranged on a downstream side of the ion exchange resin unit, and the

deaerated water production unit is arranged in a circulation route that supplies the deaerated water to a deaerated water use machine and receives used deaerated water drained from the deaerated water use machine,

wherein the deaerated water production unit is arranged on a downstream side of the microfilter and immediately upstream of the deaerated water use machine in the circulation route.

3. The water production system according to claim 1, wherein the ultrasonic oscillator generates ultrasonic waves of 0.1 to 1.0 MHz, and the depressurizer reduces the pressure to 0.2 atm or lower in the chamber.

4. The water production system according to claim 1, wherein the deaerated water production unit produces deaerated water having an oxygen content of 2.0 mg/L or lower.

5. The water production system according to claim 1, further comprising:

a temperature controller arranged on the downstream side of the ion exchange resin unit.

6. The water production system according to claim 1, further comprising:

a waste water tank arranged on an upstream side of the filter unit to hold waste water therein.

7. A wafer manufacturing method for manufacturing a wafer from an ingot, comprising:

a separation starting point forming step of forming a separation starting point by forming modified layers through irradiation of the ingot with a laser beam having a wavelength transmittable through the ingot with a focal point of the laser beam positioned at a depth from an end face of the ingot, the depth corresponding to a thickness of the wafer to be manufactured; and

a separation step of separating the wafer to be manufactured from the ingot, from the separation starting point,

wherein, in the separation step, deaerated water produced by a water production system according to any one of claims 1 to 6 is supplied to the end face of the ingot to form a layer of the deaerated water, and ultrasonic waves are applied to the ingot via the layer of the deaerated water, thereby disrupting the separation starting point, the water production system including a filter unit that filters water to produce clear water, an ultraviolet light irradiator that irradiates, with ultraviolet light, the clear water produced by the filter unit, thereby degrading organic matter in the clear water, an ion exchange resin unit that purifies the clear

water, in which the organic matter has been degraded by the ultraviolet light irradiator, into pure water, and a deaerated water production unit that deaerates the pure water to produce the deaerated water.

8. The wafer manufacturing method according to claim 7, wherein the ingot is an SiC ingot.

9. The wafer manufacturing method according to claim 8,

wherein the SiC ingot has a first surface, a second surface on an opposite side to the first surface, a c-axis extending from the first surface to the second surface, and a c-plane orthogonal to the c-axis, the c-axis is inclined with respect to a perpendicular to the first surface, and an off-angle is formed between the c-plane and the first surface, and

the separation starting point forming step includes

a modified layer forming step of forming a linear modified layer by moving the focal point of the laser beam and the SiC ingot relative to each other in a direction orthogonal to a direction in which the off-angle is formed, and

an indexing step of subjecting the focal point of the laser beam and the SiC ingot to index feeding by a predetermined amount by moving the focal point and the SiC

ingot relative to each other in the direction in which the off-angle is formed.